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(2013.01); **H01L 51/5203** (2013.01); **H01L**  
**2251/5338** (2013.01)(21) Appl. No.: **15/642,662**(22) Filed: **Jul. 6, 2017****Related U.S. Application Data**(60) Provisional application No. 62/358,760, filed on Jul.  
6, 2016.

(57)

**ABSTRACT**

Disclosed are a display apparatus and a method of manufacturing the same. The display apparatus includes a light emitting part including a plurality of light emitting diodes; and a thin film transistor (TFT) panel part configured to drive the plurality of light emitting diodes. A first side of the light emitting part and a first side of the TFT panel part are coupled to each other so as to face each other. The plurality of light emitting diodes are electrically connected to the plurality of TFTs, respectively.

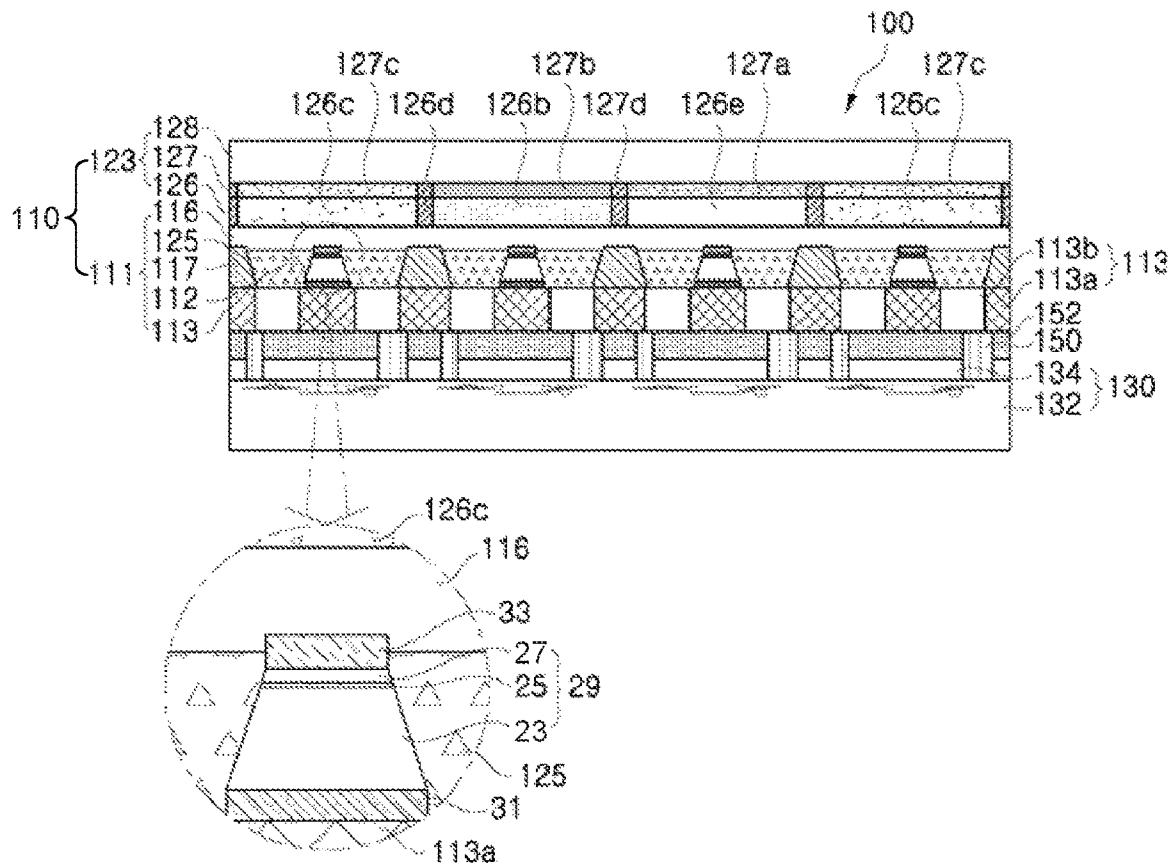


FIG. 1

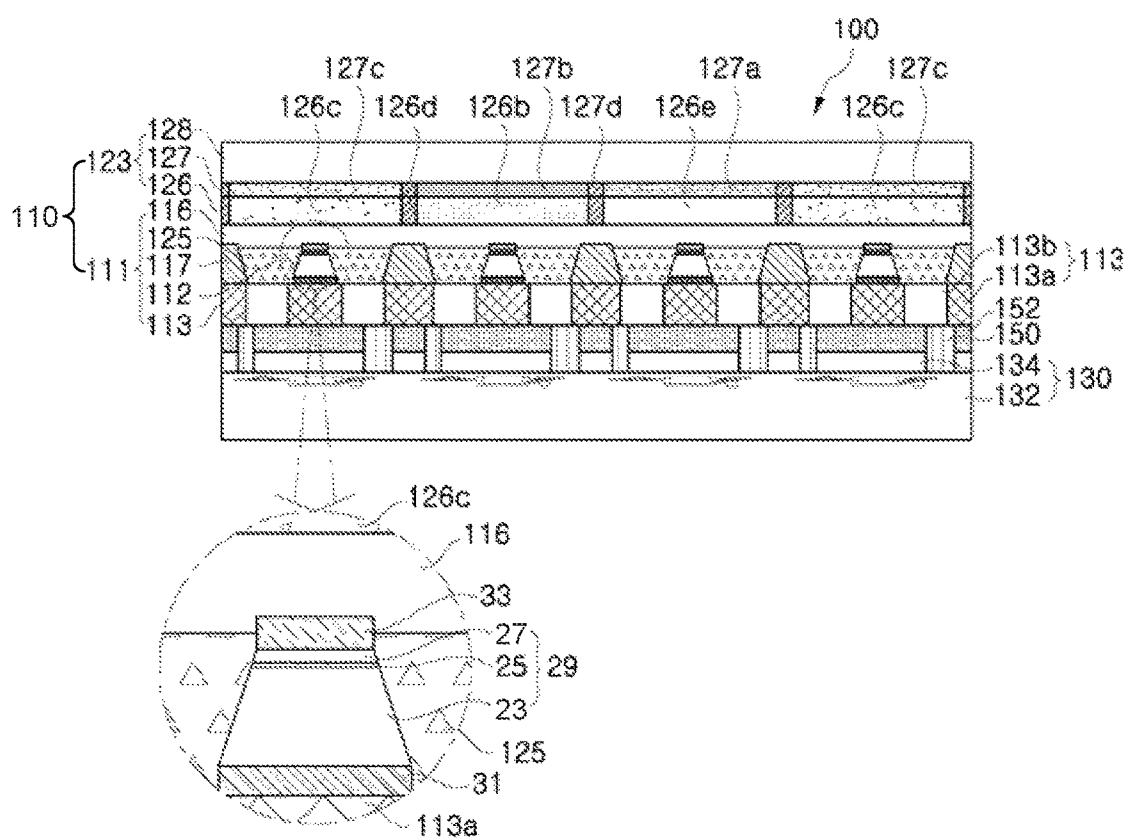


FIG. 2A



FIG. 2B

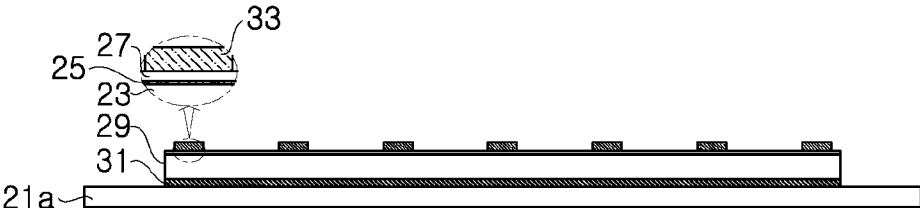


FIG. 2C

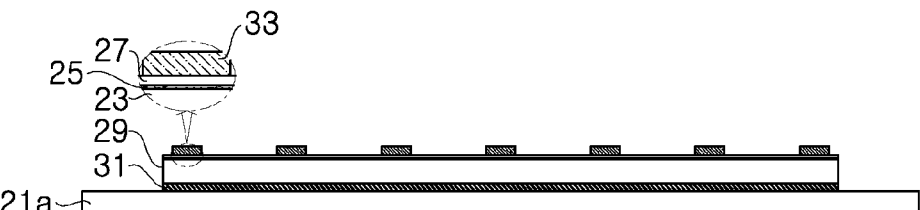


FIG. 2D

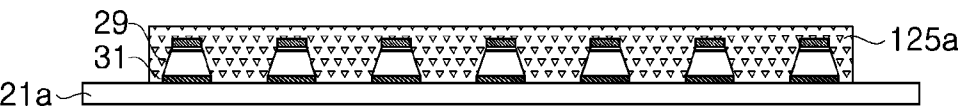


FIG. 2E

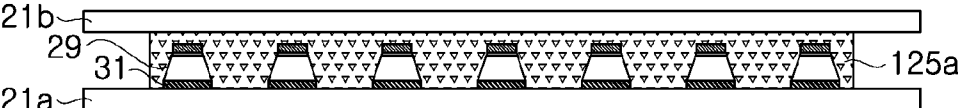


FIG. 2F

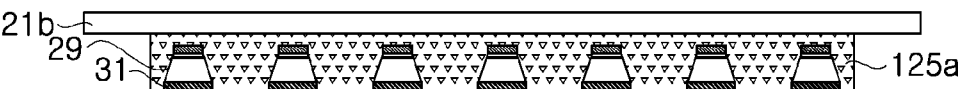


FIG. 3A

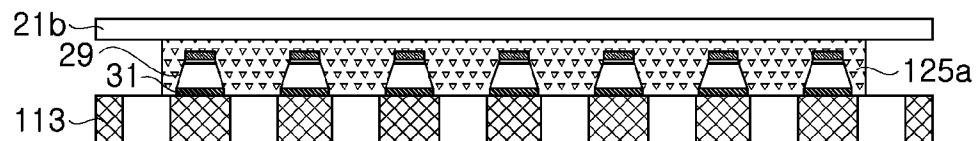


FIG. 3B

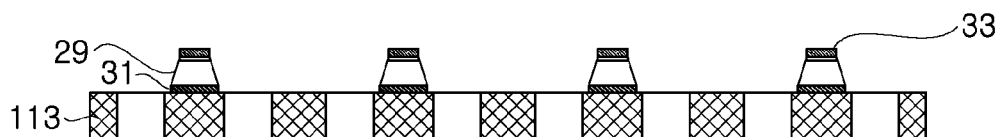


FIG. 3C

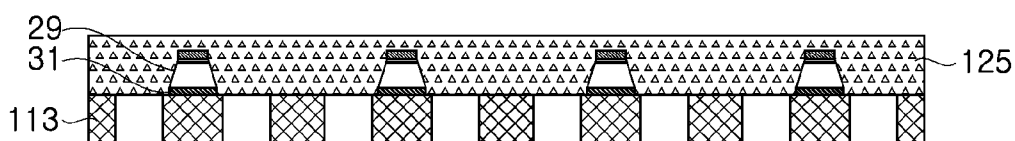


FIG. 3D

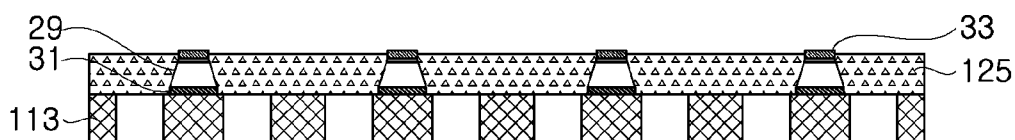


FIG. 3E

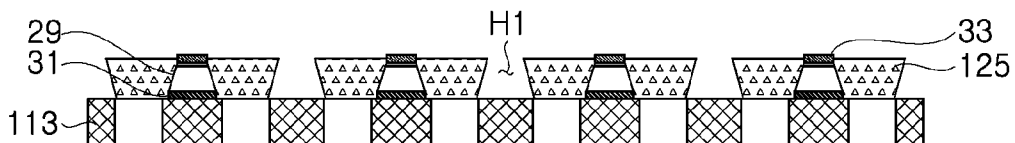


FIG. 3F

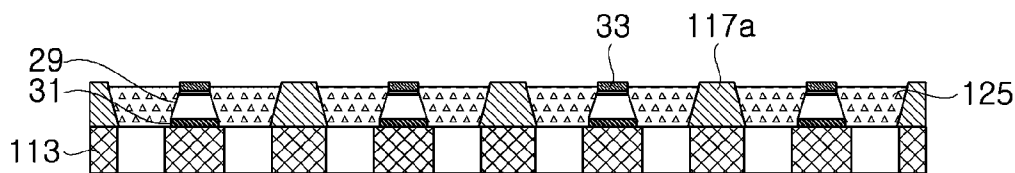


FIG. 3G

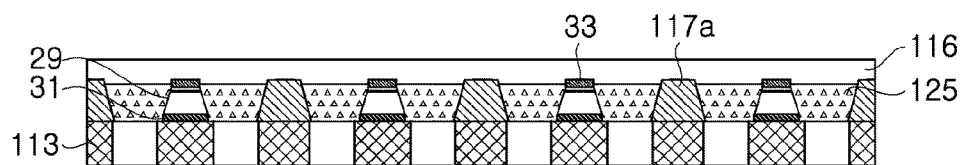


FIG. 4A

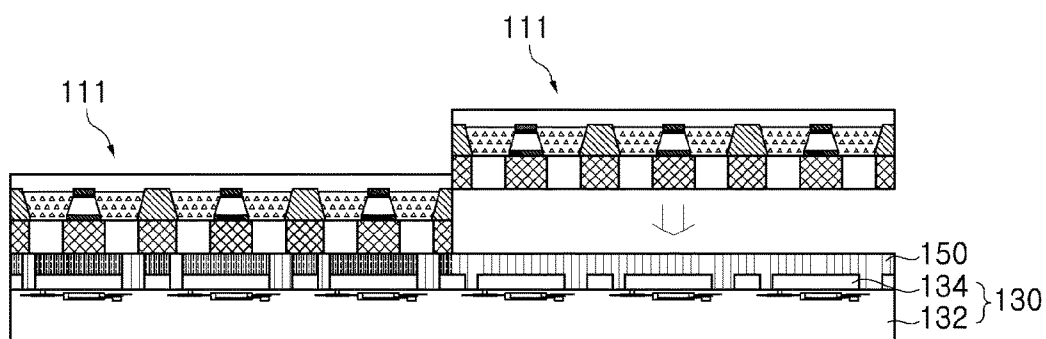


FIG. 4B

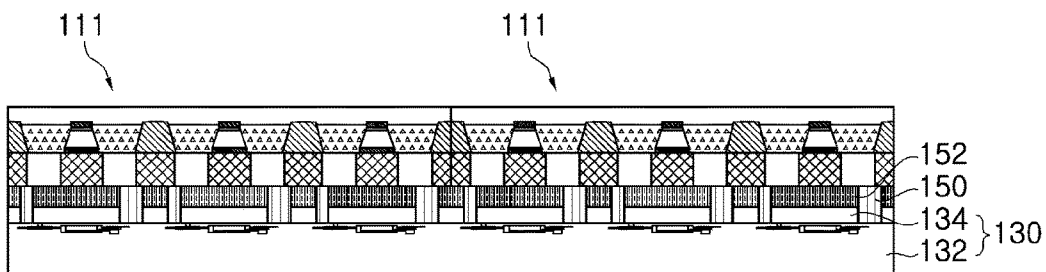


FIG. 4C

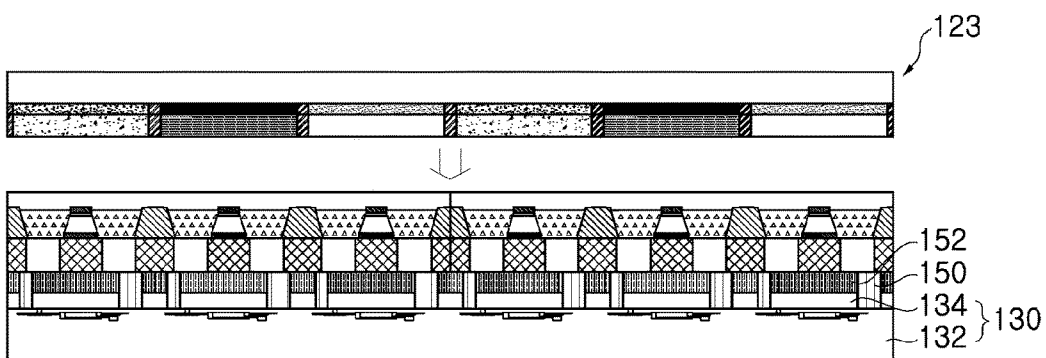




FIG. 6A



FIG. 6B

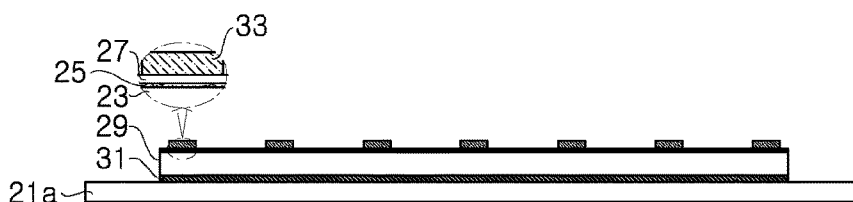


FIG. 6C

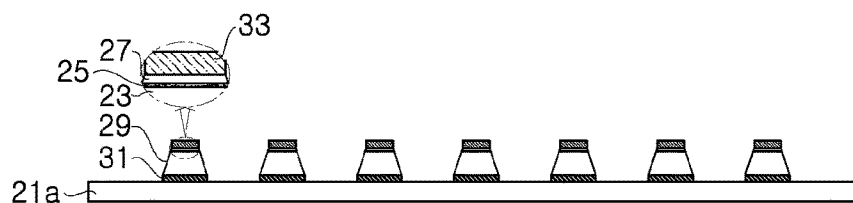


FIG. 6D

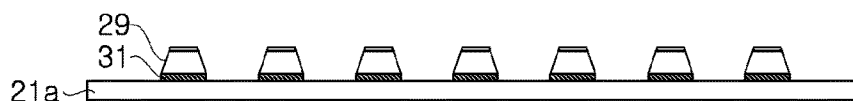


FIG. 6E

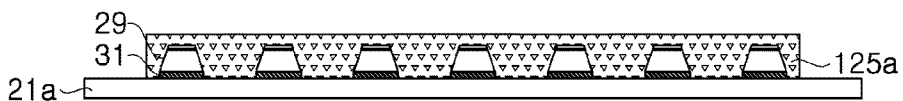


FIG. 6F

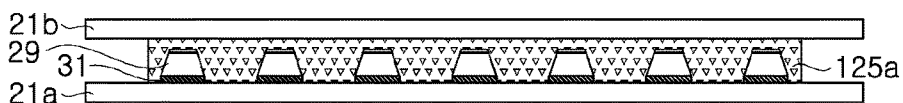


FIG. 6G

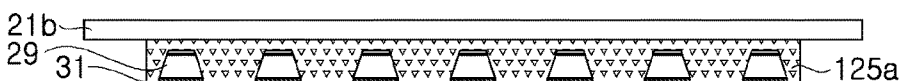


FIG. 7A

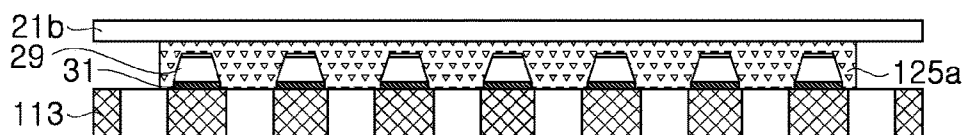


FIG. 7B

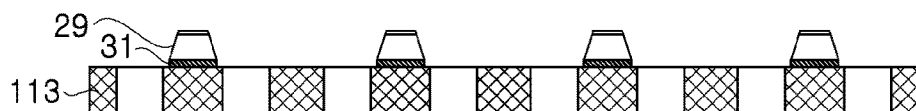


FIG. 7C

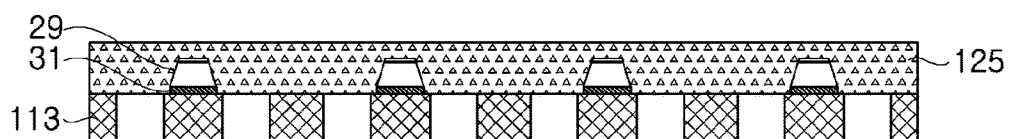


FIG. 7D

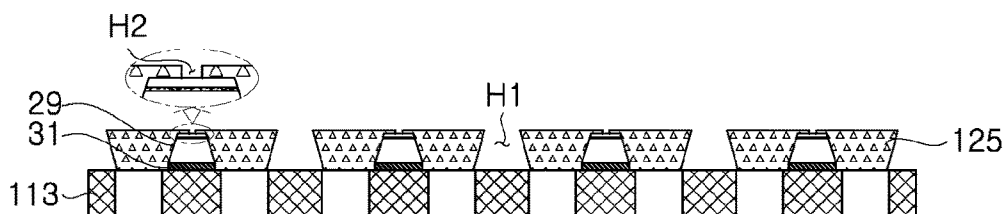


FIG. 7E

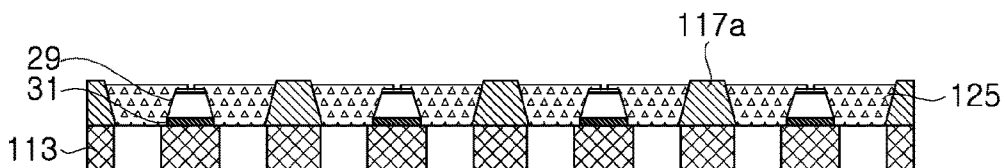


FIG. 7F

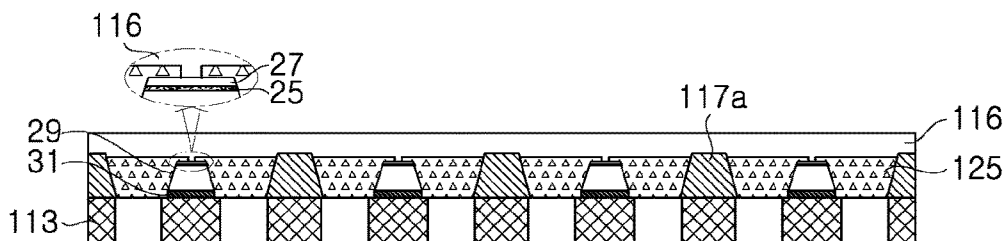




FIG. 8

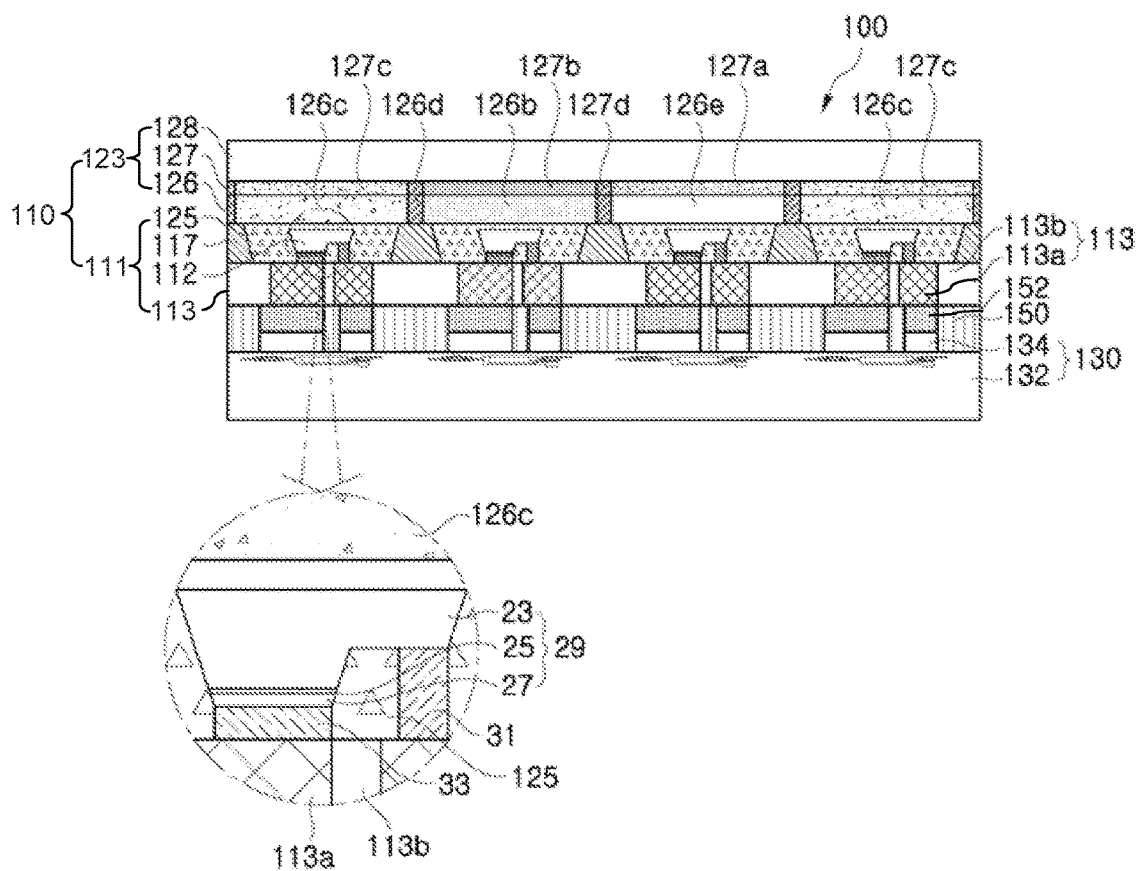


FIG. 9

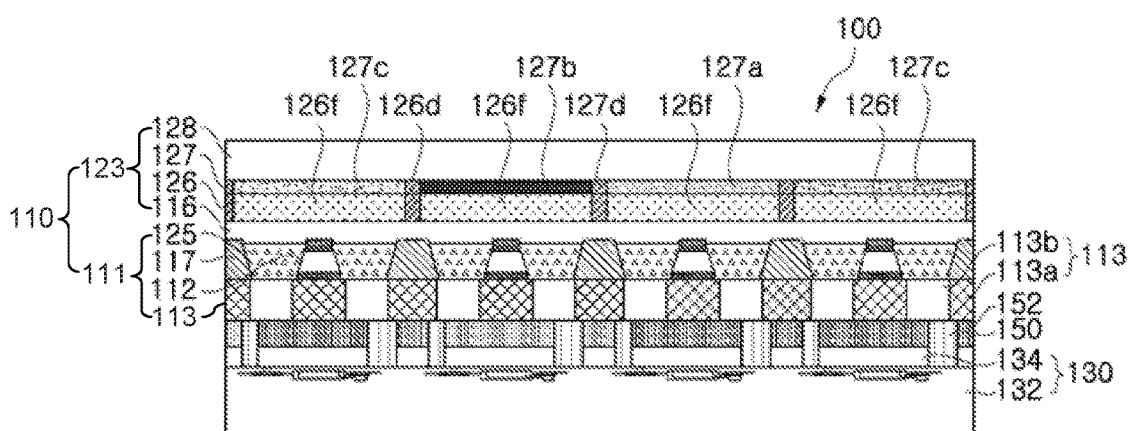


FIG 10

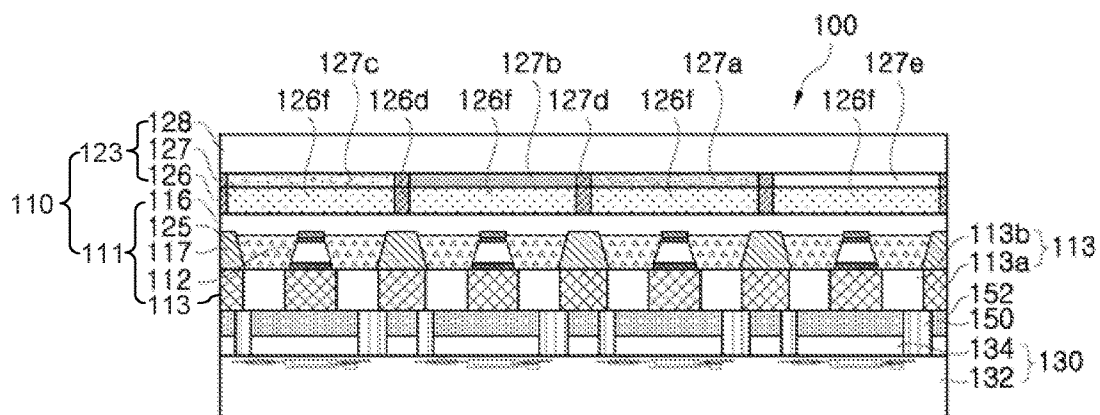


FIG 11

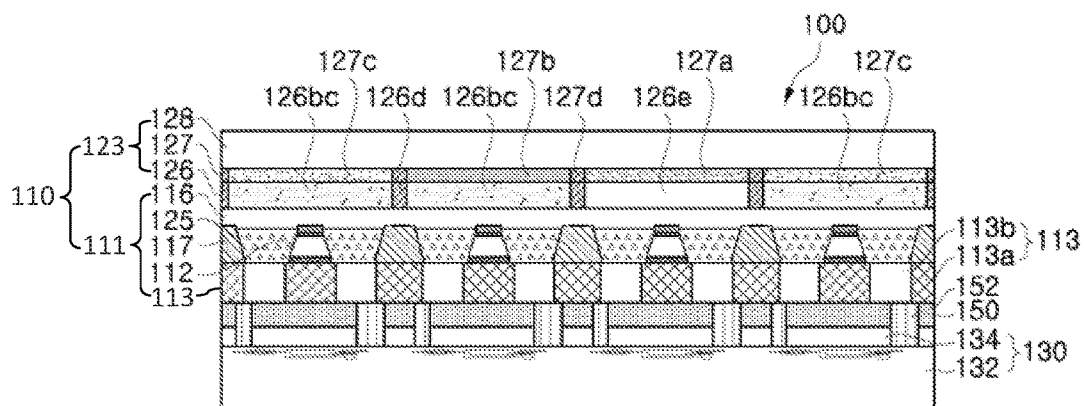
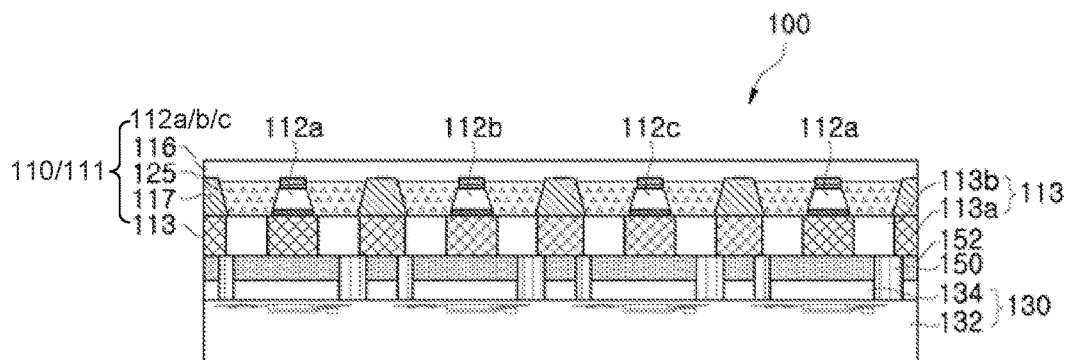


FIG 12



## DISPLAY APPARATUS

### CROSS-REFERENCE TO RELATED APPLICATION

[0001] This patent document claims priority to and the benefit of U.S. Patent Provisional Application No. 62/358,760, filed on Jul. 6, 2016, which is incorporated by reference for all purposes as if fully set forth herein.

### BACKGROUND

#### Field

[0002] Exemplary embodiments relate to a display apparatus. More particularly, exemplary embodiments relate to a display apparatus using a micro-light emitting diode or a micro-LED.

#### Discussion of the Background

[0003] A light emitting diode refers to an inorganic semiconductor device that emits light through recombination of electrons and holes. Due to light emitting diodes having remarkably long lifespans, low power consumption, and rapid response rates, light emitting diodes are also highly versatile. In recent years, light emitting diodes have been used in television displays, monitors, automobile lamps, and general lighting. As a result, a light emitting device has many advantages as a light source.

[0004] Recently, televisions or monitors generate colorful images with the use of a thin film transistor liquid crystal display (TFT-LCD) panel and light emitting diodes as a backlight source. However, in a TFT-LCD, since one LED is used as a light source for many pixels, a backlight light source must be kept on. As a result, the TFT-LCD suffers from constant power consumption regardless of brightness of a displayed screen.

[0005] Also recently, a display apparatus is often manufactured using organic light emitting diodes (OLEDs). Although power consumption of an OLED display apparatus has been continuously reduced, the OLED still requires a much higher power consumption compared to LEDs formed of inorganic semiconductors. Thus, OLED based displays generally have power efficiency less than that of LEDs.

[0006] Moreover, a passive-matrix (PM) drive type OLED display apparatus can suffer from deterioration in response speed upon pulse amplitude modulation (PAM) of the OLED having large capacitance. In addition, the PMOLED display apparatus can suffer from deterioration in lifespan upon high current driving through pulse width modulation (PWM) for realizing a low duty ratio.

[0007] Furthermore, an active-matrix (AM) driving type OLED display apparatus requires connection of TFTs for each pixel. Thus, the AMOLED display apparatus requires higher manufacturing costs and has non-uniform brightness according to characteristics of TFTs.

### SUMMARY

[0008] Exemplary embodiments provide a display apparatus using micro-light emitting diodes having low power consumption. These exemplary embodiments may be used in wearable apparatuses, a smartphones, tablet, television, etc.

[0009] Exemplary embodiments provide a display apparatus having a large area.

[0010] In accordance with one aspect, a display apparatus includes a light emitting part including a plurality of light emitting diodes; and a thin film transistor (TFT) panel part including a plurality of TFTs configured to drive the plurality of light emitting diodes. A first side of the light emitting part and a first side of the TFT panel part are coupled to each other so as to face each other. The light emitting diodes are electrically connected to the TFTs, respectively.

[0011] In accordance with another aspect, a display apparatus includes a plurality of light emitting parts each including a plurality of light emitting diodes; and a thin film transistor (TFT) panel part including a plurality of TFTs configured to drive the plurality of light emitting diodes. A first side of the plurality of light emitting parts is coupled to a first side of the TFT panel part so as to face each other and the plurality of light emitting diodes are electrically connected to some of the plurality of TFTs, respectively.

[0012] According to exemplary embodiments, the display apparatus employs micro-light emitting diodes formed of nitride semiconductors to realize high resolution, low power consumption, and high efficiency so as to be applicable to a wearable apparatus.

[0013] In addition, the display apparatus according to the exemplary embodiments allows light emitted from side surfaces of the light emitting diodes to be discharged through reflection by reflective electrodes, thereby enabling reduction in thickness of the light emitting part.

[0014] Further, when the light emitting diodes of the display apparatus according to the exemplary embodiments have a diameter of greater than 10  $\mu\text{m}$ , the display apparatus allows light emitted through upper and side surfaces of the light emitting diodes to be discharged to the outside, thereby improving luminous efficacy.

[0015] Further, the display apparatus according to exemplary embodiments allows a plurality of light emitting parts having a plurality of pixels to be mounted on a large TFT panel part such that each of the light emitting parts having confirmed performance can be used in manufacture of a large display apparatus, thereby minimizing failure in manufacture of the display apparatus while improving yield.

### BRIEF DESCRIPTION OF DRAWINGS

[0016] The accompanying drawings, which are included to provide a further understanding of the disclosed technology, and are incorporated in and constitute a part of this specification, illustrate exemplary embodiments of the disclosed technology, and together with the description serve to describe the principles of the disclosed technology.

[0017] FIG. 1 is a sectional view of a display apparatus according to a first exemplary embodiment.

[0018] FIG. 2A, FIG. 2B, FIG. 2C, FIG. 2D, FIG. 2E, and FIG. 2F are sectional views illustrating a process of manufacturing light emitting diodes of the display apparatus according to the first exemplary embodiment.

[0019] FIG. 3A, FIG. 3B, FIG. 3C, FIG. 3D, FIG. 3E, FIG. 3F, and FIG. 3G are sectional views illustrating a process of manufacturing a light emitting part of the display apparatus according to the first exemplary embodiment.

[0020] FIG. 4A, FIG. 4B, and FIG. 4C are sectional views illustrating a process of coupling the light emitting part, a light conversion part and a TFT panel part of the display apparatus according to the first exemplary embodiment.

[0021] FIG. 5 is a sectional view of a display apparatus according to a second exemplary embodiment.

**[0022]** FIG. 6A, FIG. 6B, FIG. 6C, FIG. 6D, FIG. 6E, FIG. 6F, and FIG. 6G are sectional views illustrating a process of manufacturing light emitting diodes of the display apparatus according to the second exemplary embodiment.

**[0023]** FIG. 7A, FIG. 7B, FIG. 7C, FIG. 7D, FIG. 7E, and FIG. 7F are sectional views illustrating a process of manufacturing a light emitting part of the display apparatus according to the second exemplary embodiment.

**[0024]** FIG. 8 is a sectional view of a display apparatus according to a third exemplary embodiment.

**[0025]** FIG. 9 is a sectional view of a display apparatus according to a fourth exemplary embodiment.

**[0026]** FIG. 10 is a sectional view of a display apparatus according to a fifth exemplary embodiment.

**[0027]** FIG. 11 is a sectional view of a display apparatus according to a sixth exemplary embodiment.

**[0028]** FIG. 12 is a sectional view of a display apparatus according to a seventh exemplary embodiment.

#### DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENTS

**[0029]** In the following description, for the purposes of explanation, numerous specific details are set forth in order to provide a thorough understanding of various exemplary embodiments. It is apparent, however, that various exemplary embodiments may be practiced without these specific details or with one or more equivalent arrangements. In other instances, well-known structures and devices are shown in block diagram form in order to avoid unnecessarily obscuring various exemplary embodiments.

**[0030]** Unless otherwise specified, the illustrated exemplary embodiments are to be understood as providing exemplary features of varying detail of various exemplary embodiments. Therefore, unless otherwise specified, the features, components, modules, layers, films, panels, regions, and/or aspects of the various illustrations may be otherwise combined, separated, interchanged, and/or rearranged without departing from the disclosed exemplary embodiments. Further, in the accompanying figures, the size and relative sizes of layers, films, panels, regions, etc., may be exaggerated for clarity and descriptive purposes. Also, like reference numerals denote like elements.

**[0031]** When an element or layer is referred to as being “on,” “connected to,” or “coupled to” another element or layer, it may be directly on, connected to, or coupled to the other element or layer or intervening elements or layers may be present. When, however, an element or layer is referred to as being “directly on,” “directly connected to,” or “directly coupled to” another element or layer, there are no intervening elements or layers present. For the purposes of this disclosure, “at least one of X, Y, and Z” and “at least one selected from the group consisting of X, Y, and Z” may be construed as X only, Y only, Z only, or any combination of two or more of X, Y, and Z, such as, for instance, XYZ, XYY, YZ, and ZZ. As used herein, the term “and/or” includes any and all combinations of one or more of the associated listed items.

**[0032]** Although the terms “first,” “second,” etc. may be used herein to describe various elements, components, regions, layers, and/or sections, these elements, components, regions, layers, and/or sections should not be limited by these terms. These terms are used to distinguish one element, component, region, layer, and/or section from another element, component, region, layer, and/or section. Thus, a first

element, component, region, layer, and/or section discussed below could be termed a second element, component, region, layer, and/or section without departing from the teachings of the present disclosure.

**[0033]** Spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper,” and the like, may be used herein for descriptive purposes, and, thereby, to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the drawings. Spatially relative terms are intended to encompass different orientations of an apparatus in use, operation, and/or manufacture in addition to the orientation depicted in the drawings. For example, if the apparatus in the drawings is turned over, elements described as “below” or “beneath” other elements or features would then be oriented “above” the other elements or features. Thus, the exemplary term “below” can encompass both an orientation of above and below. Furthermore, the apparatus may be otherwise oriented (e.g., rotated 90 degrees or at other orientations), and, as such, the spatially relative descriptors used herein interpreted accordingly.

**[0034]** The terminology used herein is for the purpose of describing particular embodiments and is not intended to be limiting. As used herein, the singular forms, “a,” “an,” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. Moreover, the terms “comprises,” “comprising,” “includes,” and/or “including,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, components, and/or groups thereof, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

**[0035]** Various exemplary embodiments are described herein with reference to sectional illustrations that are schematic illustrations of idealized exemplary embodiments and/or intermediate structures. As such, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, exemplary embodiments disclosed herein should not be construed as limited to the particular illustrated shapes of regions, but are to include deviations in shapes that result from, for instance, manufacturing. The regions illustrated in the drawings are schematic in nature and their shapes are not intended to illustrate the actual shape of a region of a device and are not intended to be limiting.

**[0036]** Unless otherwise defined, all terms (including technical and scientific terms) used herein have the same meaning as commonly understood by one of ordinary skill in the art to which this disclosure is a part. Terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and will not be interpreted in an idealized or overly formal sense, unless expressly so defined herein.

**[0037]** Exemplary embodiments of the present disclosure will be described in more detail with reference to the accompanying drawings.

**[0038]** FIG. 1 is a sectional view of a display apparatus according to a first exemplary embodiment of the present disclosure.

**[0039]** Referring to FIG. 1, the display apparatus 100 according to the first exemplary embodiment includes a light

emitting diode part **110**, a TFT panel part **130**, and an anisotropic conductive film **150**.

[0040] The light emitting diode part **110** includes a light emitting part **111** and a light conversion part **123**. The light emitting part **111** includes light emitting diodes **112**, a connection substrate **113**, a transparent electrode **116**, reflective electrodes **117**, and an encapsulation material **125**. The light conversion part **123** includes a phosphor layer **126**, a color filter **127**, and a protective substrate **128**.

[0041] The light emitting diode part **110** includes a plurality of light emitting diodes **112**, which are regularly arranged with reference to the connection substrate **113**. For example, the plurality of light emitting diodes **112** may be arranged at constant intervals in rows and columns. In this exemplary embodiment, the plurality of light emitting diodes **112** may include light emitting diodes emitting blue light or UV light.

[0042] In the display apparatus **100** according to this exemplary embodiment, the light emitting diode part **110** can be driven by power applied from an exterior power source to each of the light emitting diodes **112**. That is, each of the light emitting diodes **112** can be turned on or off in combination and light emitted from each of the light emitting diodes **112** is converted into red light, green light and blue light while passing through the light conversion part **123**. Accordingly, the light emitting diode part **110** of the display apparatus **100** can be driven without a separate LCD.

[0043] In this exemplary embodiment, a region including a single light emitting diode **112** may be used as a subpixel in the display apparatus **100** and one pixel may be composed of three or four subpixels. In the light emitting diode part, one subpixel may have a larger size than the light emitting diode **112** disposed in the subpixel.

[0044] Referring to FIG. 1, each of the light emitting diodes **112** includes an n-type semiconductor layer **23**, an active layer **25**, a p-type semiconductor layer **27**, an n-type electrode **31**, and a p-type electrode **33**. Here, a light emitting structure **29** including the n-type semiconductor layer **23**, the active layer **25** and the p-type semiconductor layer **27** may include Group III-V based compound semiconductors. By way of example, these semiconductor layers may include nitride semiconductors such as (Al, Ga, In)N. In other exemplary embodiments, locations of the n-type semiconductor layer **23** and the p-type semiconductor layer **27** can be interchanged.

[0045] The n-type semiconductor layer **23** may include an n-type dopant (for example, Si) and the p-type semiconductor layer **27** may include a p-type dopant (for example, Mg). The active layer **25** is interposed between the n-type semiconductor layer **23** and the p-type semiconductor layer **27**. The active layer **25** may have a multi-quantum well (MQW) structure and the composition of the active layer **25** may be determined so as to emit light having a desired peak wavelength.

[0046] In this exemplary embodiment, the light emitting structure **29** including the n-type semiconductor layer **23**, the active layer **25** and the p-type semiconductor layer **27** may have the shape of a vertical type light emitting diode. In this structure, the n-type electrode **31** may be disposed on an outer surface of the n-type semiconductor layer **23** and the p-type electrode **33** may be disposed on an outer surface of the p-type semiconductor layer **27**.

[0047] In addition, each of the n-type electrode **31** and the p-type electrode **33** may be formed of an opaque metal. In

this exemplary embodiment, the n-type electrode **31** formed of an opaque metal is disposed to cover the entirety of the n-type semiconductor layer **23**, whereby light generated in the active layer **25** can be reflected by the n-type electrode **31** to be discharged through a side surface of the n-type semiconductor layer **23** even when passing through the n-type semiconductor layer **23**.

[0048] Further, the p-type electrode **33** is disposed to cover the entirety of the p-type semiconductor layer **27**. Like the n-type electrode **31**, the p-type electrode **33** may include an opaque metal, whereby light generated in the active layer **25** can be reflected by the p-type electrode **33** to be discharged through a side surface of the p-type semiconductor layer **27** even when passing through the p-type semiconductor layer **27**.

[0049] In this exemplary embodiment, the p-type electrode **33** is disposed to cover the entirety of the p-type semiconductor layer **27** and a contact region between the p-type semiconductor layer **27** and the p-type electrode **33** may have a width of 10  $\mu\text{m}$  or less. That is, the contact region between the p-type electrode **33** and the p-type semiconductor layer **27** may have an area of 100  $\mu\text{m}^2$  or less. In this structure wherein the contact area between the p-type electrode **33** and the p-type semiconductor layer **27** is 100  $\mu\text{m}^2$  or less, it is possible to maintain current density of a certain level even when a small amount of current is supplied through the p-type electrode **33**.

[0050] As described above, in the structure wherein the n-type electrode **31**, the insulating layer **37** and the p-type electrode **33** are disposed to cover the entirety of the n-type semiconductor layer **23** and the p-type semiconductor layer **27**, light emitted from the active layer **25** can be discharged only through the side surface of the light emitting structure **29** instead of being discharged towards the n-type semiconductor layer **23** or the p-type semiconductor layer **27** (that is, in the vertical direction). Here, the n-type electrode **31** and the p-type electrode **33** may include a metal (for example, Al or Ag) that allows improvement in reflection efficiency while allowing power to be supplied to the light emitting structure **29**.

[0051] The connection substrate **113** serves to support the light emitting part **111** and may be selected from various substrates. In this exemplary embodiment, the connection substrate **113** may be an insulating substrate that exhibits conductivity at some parts thereof. That is, although most of the connection substrate **113** exhibits insulation properties, some portions of the connection substrate **113** adjoining the light emitting diodes **112** and the reflective electrodes **117** can exhibit conductivity. In this exemplary embodiment, the connection substrate **113** includes conductive portions **113a** formed from an upper surface thereof to a lower surface thereof through the connection substrate **113** to allow electrical conduction between the upper surface of the connection substrate **113** and the lower surface thereof. The connection substrate **113** may have a structure in which a plurality of holes is formed through an electrically insulating substrate to extend from an upper surface of the substrate to a lower surface thereof and is filled with a conductive material (for example, Cu). Here, the conductive portions **113a** formed in the connection substrate **113** may be electrically insulated from one another by the insulating portions **113b**.

[0052] In this exemplary embodiment, the connection substrate **113** may be a flexible substrate. Accordingly, the

connection substrate **113** can be coupled to a planar TFT panel part **130** or a curved TFT panel part **130**. In this exemplary embodiment, the insulating portions **113b** of the connection substrate **113** may include polydimethylsiloxane (PDMS), polyimide, ceramic, or a mixture thereof. The conductive portions **113a** may include a metal having high electrical conductivity (for example, copper (Cu), gold (Au), or silver (Ag)).

[0053] After the connection substrate **113** is formed, the light emitting diodes **112** are disposed on the conductive portions **113a** of the connection substrate **113**. In this exemplary embodiment, the n-type electrodes **31** of the light emitting diodes **112** contact the conductive portions **113a** of the connection substrate **113**, without being limited thereto. Alternatively, the p-type electrodes **33** may be disposed to contact the conductive portions **113a** of the connection substrate **113**, as needed. Further, in the connection substrate **113**, the reflective electrodes **117** may electrically contact other conductive portions **113a** disposed near the conductive portions **113a** contacting the light emitting diodes **112**.

[0054] Further, in the connection substrate **113**, the conductive portions **113a** exhibit electrical conductivity, the insulating portions **113b** exhibit electrical insulating properties, and both the conductive portions **113a** and the insulating portions **113b** may include a material capable of reflecting light emitted from the light emitting diodes **112**. Accordingly, light emitted from the light emitting diodes **112** can be reflected by the connection substrate **113** towards the reflective electrodes **117** or in an upward direction.

[0055] The transparent electrode **116** may electrically contact the p-type electrodes **33** of the light emitting diodes **112** and may also electrically contact the reflective electrodes **117**. With this structure, power supplied from the reflective electrodes **117** can be supplied to the p-type electrodes **33**. In this exemplary embodiment, the transparent electrode **116** may be transparent to allow light emitted from the light emitting diodes **112** to be directed to the light conversion part **123** therethrough and may be formed as thin as possible. In this exemplary embodiment, the transparent electrode **116** may be formed of ITO.

[0056] Each of the reflective electrodes **117** may have a predetermined thickness and be disposed to surround the light emitting diode **112**. The reflective electrode **117** is disposed to surround the side surface of the light emitting diode **112**. Thus, the size of one subpixel may be determined by the reflective electrode **117**.

[0057] In this exemplary embodiment, each reflective electrode **117** may be separated from the side surface of the light emitting diode **112** by a predetermined distance and have an inclined side surface facing the light emitting diode **112**, as shown in FIG. 1. Here, the inclined surface of the reflective electrode **117** may be sloped in a direction capable of reflecting light emitted from the light emitting diode **112** towards the transparent electrode **116**.

[0058] Further, as described above, each reflective electrode **117** may have a sidewall formed to set a region for one subpixel and integrated with a sidewall of another subpixel adjacent to the corresponding subpixel. That is, the reflective electrodes **117** may be disposed such that upper portions of the reflective electrodes **117** divide the transparent electrode **116** into a plurality of regions while adjoining to the transparent electrode **116** and lower portions of the reflective electrodes **117** may electrically contact the conductive portions **113a** of the connection substrate **113**.

[0059] Each of the regions divided by the reflective electrodes **117** acts as a subpixel in the display apparatus **100** and each subpixel may be provided with at least one light emitting diode **112**.

[0060] The encapsulation material **125** may fill the subpixel regions defined by the reflective electrodes **117**. With this structure, the encapsulation material **125** may be disposed to cover the entirety of the light emitting diodes **112** and may be formed of a transparent material that exhibits electrical insulating properties. Accordingly, light emitted from the light emitting diodes **112** can be discharged through the encapsulation material **125**.

[0061] As described above, the light conversion part **123** includes the phosphor layer **126**, the color filter **127**, and the protective substrate **128**.

[0062] The phosphor layer **126** may be disposed on the protective substrate **128** and may include a green phosphor layer **126b**, a red phosphor layer **126c**, and a transparent layer **126e**. The green phosphor layer **126b**, the red phosphor layer **126c** and the transparent layer **126e** are alternately arranged to be adjacent to each other and separated from each other by a predetermined distance or more. In addition, a blocking layer **126d** may be disposed between the green phosphor layer **126b**, the red phosphor layer **126c**, and the transparent layer **126e**. Accordingly, the blocking layer **126d** can prevent mixture of light by preventing light having entered the green phosphor layer **126b**, the red phosphor layer **126c**, or the transparent layer **126e** from entering other phosphor layers.

[0063] Although the blue light emitting diodes are illustrated as the light emitting diodes **112** in this exemplary embodiment, the light emitting diodes **112** may emit light having a peak wavelength (for example, 360 nm to 470 nm) in the blue light range or in the near UV range.

[0064] Accordingly, the green phosphor layer **126b** emits green light through wavelength conversion of blue light emitted from the light emitting diodes **112** and the red phosphor layer **126c** emits red light through wavelength conversion of blue light emitted from the light emitting diodes **112**. The transparent layer **126e** allows blue light emitted from blue light emitting diode to be discharged therethrough without wavelength conversion.

[0065] In the structure wherein the light emitting diodes **112** are UV light emitting diodes, a blue phosphor layer may be disposed at the location of the transparent layer **126e** instead of the transparent layer **126e**. In this structure, UV light emitted from the light emitting diodes **112** is converted into blue light while passing through the blue phosphor layer such that blue light can be discharged to the outside.

[0066] In this exemplary embodiment, the color filter **127** may be interposed between the phosphor layer **126** and the protective substrate **128**. The color filter **127** may include a blue light portion **127a**, a green light portion **127b**, a red light portion **127c**, and a light blocking portion **127d**. The color filter **127** may be formed in a film shape and can block light having passed through the color filter **127** excluding light of a certain wavelength.

[0067] That is, the blue light portion **127a** allows only blue light to pass therethrough by blocking light having other wavelengths excluding the wavelength of blue light, and the green light portion **127b** allows only green light to pass therethrough by blocking light having other wavelengths excluding the wavelength of green light. The red light portion **127c** allows only red light to pass therethrough by

blocking light having other wavelengths excluding the wavelength of red light. The light blocking portion **127d** is disposed between the blue light portion **127a**, the green light portion **127b** and the red light portion **127c**, and blocks all wavelengths of light.

**[0068]** The blue light portion **127a** of the color filter **127** is disposed on the transparent layer **126e** of the phosphor layer **126** and the green light portion **127b** of the color filter **12** is disposed on the green phosphor layer **126b** of the phosphor layer **126**. In addition, the red light portion **127c** of the color filter **12** is disposed on the red phosphor layer **126c** of the phosphor layer **126**. Accordingly, light emitted from the light emitting diodes **112** is subjected to wavelength conversion while passing through the phosphor layer **126**, whereby blue light, green light and red light can be separately discharged to the outside through the color filter **127**. By way of example, although blue light emitted from the light emitting diodes **112** is converted into green light through the green phosphor layer **126b**, some fraction of the blue light can pass through the phosphor layer **126** without wavelength conversion. The blue light having passed through the phosphor layer **126** without wavelength conversion is blocked by the green light portion **127b** of the color filter **127** such that only green light can be discharged through the green light portion **127b** of the color filter **127**.

**[0069]** The protective substrate **128** is disposed to contact the color filter **127** and can protect the color filter **127** from the outside by preventing the color filter **127** from being directly exposed. In this exemplary embodiment, the protective substrate **128** may be formed of a transparent material through which light can pass.

**[0070]** The TFT panel part **130** is coupled to the light emitting part **111** and serves to supply power to the light emitting part **111**. To this end, the TFT panel part **130** includes a panel substrate **132** and connection electrodes **134**. The TFT panel part **130** can control power supply to the light emitting diode part **110** to allow only some of the light emitting diodes **112** in the light emitting diode part **110** to emit light and can control the intensity of light emitted from the light emitting diodes **112**.

**[0071]** The panel substrate **132** may have a TFT drive circuit therein. The TFT drive circuit may be a circuit for driving an active matrix (AM) or a circuit for driving a passive matrix (PM).

**[0072]** The connection electrodes **134** are electrically connected to the TFT drive circuit of the panel substrate **132** and to the light emitting diodes **112** or the reflective electrodes **117** of the light emitting diode part **110**. That is, multiple connection electrodes **134** may be provided and they may be separated from each other. Power supplied through the TFT drive circuit can be supplied to each of the light emitting diodes **112** through the connection electrodes **134** and the reflective electrodes **117**. In this exemplary embodiment, the connection electrodes **134** may be covered by a separate protective layer, which may include, for example,  $\text{SiN}_x$ .

**[0073]** The anisotropic conductive film **150** serves to electrically connect the light emitting diode part **110** to the TFT panel part **130**. The anisotropic conductive film **150** may include an adhesive organic insulating material and may contain conductive particles uniformly dispersed therein to achieve electrical connection. The anisotropic conductive film **150** exhibits electrical conductivity in the thickness direction thereof and insulating properties in the plane direction thereof. In addition, the anisotropic conduc-

tive film **150** exhibits adhesive properties. With this structure, the anisotropic conductive film **150** can bond the light emitting part **111** to the TFT panel part **130** such that the light emitting part **111** can be electrically connected to the TFT panel part **130** therethrough.

**[0074]** Particularly, the anisotropic conductive film **150** may be advantageously used to connect ITO electrodes which are difficult to solder at high temperature.

**[0075]** As such, in the structure wherein the light emitting part **111** is coupled to the TFT panel part **130** via the anisotropic conductive film **150**, the connection substrate **113** can be electrically connected to the connection electrodes **134** of the TFT panel part **130** via an electrode connection portion **152**.

**[0076]** In this exemplary embodiment, the light emitting part **111** and the TFT panel part **130** may be individually manufactured and a process of coupling the light emitting part **111** to the TFT panel part **130** will be described below.

**[0077]** FIG. 2A, FIG. 2B, FIG. 2C, FIG. 2D, FIG. 2E, and FIG. 2F are sectional views illustrating a process of manufacturing light emitting diodes of the display apparatus according to the first exemplary embodiment.

**[0078]** Referring to FIGS. 2A-2F, the process of manufacturing the plurality of light emitting diodes **112** will be described. Referring to FIG. 2A, an n-type electrode **31** having a predetermined area is disposed on a first manufacturing substrate **21a**, and an n-type semiconductor layer **23**, an active layer **25** and a p-type semiconductor layer **27** are sequentially stacked on the n-type electrode **31**. The first manufacturing substrate **21a** may be a sapphire substrate, a gallium nitride substrate, a glass substrate, a silicon carbide substrate, a silicon substrate, a metal substrate, a ceramic substrate, or the like.

**[0079]** Referring to FIG. 2B, a plurality of p-type electrodes **33** is disposed on the p-type semiconductor layer **27**. In this exemplary embodiment, the p-type electrodes **33** may be separated from each other by a predetermined distance.

**[0080]** After formation of the p-type electrodes **33**, the p-type semiconductor layer **27**, the active layer **25**, the n-type semiconductor layer **23** and the n-type electrode **31** are etched with respect to each of the p-type electrodes **33**. As a result, a plurality of light emitting diodes **112** can be formed on the first manufacturing substrate **21a**, as shown in FIG. 2C. In this exemplary embodiment, each of the light emitting diodes **112** may include a trapezoidal light emitting structure **29**.

**[0081]** In order to transfer the plurality of light emitting diodes **112** to the connection substrate **113**, the plurality of light emitting diodes **112** is covered with a filler **125a**, as shown in FIG. 2D. Then, referring to FIG. 2E, a second manufacturing substrate **21b** is bonded to an upper side of the filler **125a**. The second manufacturing substrate **21b** may be the same substrate as the first manufacturing substrate **21a** or may be a different substrate than the first manufacturing substrate, as needed. After the second manufacturing substrate **21b** is coupled to the upper side of the filler **125a**, the first manufacturing substrate **21a** is removed, as shown in FIG. 2F.

**[0082]** FIG. 3A, FIG. 3B, FIG. 3C, FIG. 3D, FIG. 3E, FIG. 3F, and FIG. 3G are sectional views illustrating a process of manufacturing the light emitting diode part of the display apparatus according to the first exemplary embodiment.

**[0083]** The light emitting part **111** may be manufactured using the plurality of light emitting diodes **112** manufactured

by the process shown in FIGS. 2A-2F. As shown in FIG. 3A, the connection substrate 113 is brought into contact with the plurality of light emitting diodes 112 attached to the second manufacturing substrate 21b. Here, a bonding agent may be applied to part of an upper surface of the connection substrate 113. The bonding agent may be applied to some of the conductive portions 113a of the connection substrate 113. As a result, among the plurality of light emitting diodes 112, only the light emitting diodes 112 contacting the bonding agent can be coupled to the connection substrate 113.

[0084] FIG. 3B shows the plurality of light emitting diodes 112 coupled to the connection substrate 113. That is, in this exemplary embodiment, the plurality of light emitting diodes 112 may be coupled to the connection substrate 113 such that one light emitting diode is provided to one subpixel.

[0085] After the plurality of light emitting diodes 112 is coupled to the connection substrate 113, an encapsulation material 125 may be formed to cover each of the light emitting diodes 112 and the connection electrodes 134. The encapsulation material 125 may be formed of an electrically insulating material and may be transparent. FIG. 3C shows the encapsulation material 125 formed to cover each of the light emitting diodes 112.

[0086] Next, referring to FIG. 3D, the encapsulation material 125 is subjected to etching to expose upper surfaces of the p-type electrodes 33. Etching of the encapsulation material 125 may be performed to expose only part of the upper surfaces of the p-type electrodes 33 without exposing the p-type semiconductor layer 27.

[0087] Then, referring to FIG. 3E, with reference to the exposed regions of the p-type electrodes 33, each region between the light emitting diodes 112 is subjected to etching to form a first blind-hole H1. The shape of the subpixel may be determined by the first blind-hole H1. That is, since the encapsulation material 125 is etched such that an inner side surface of the first blind-hole H becomes an inclined surface, a plurality of mesas may be formed on the connection electrodes 134. In this exemplary embodiment, one mesa may receive at least one light emitting diode 112 therein and the encapsulation material 125 may be configured to surround at least one light emitting diode 112.

[0088] After the first blind-holes H1 are formed as described above, reflective electrodes 117 are formed to fill the first blind-holes H1, as shown in FIG. 3F. Each of the reflective electrodes 117 may be formed in the first blind-hole H1 so as to correspond to the shape of the first blind-hole such that the reflective electrode 117 can have an inclined side surface corresponding to the shape of the side surface of the first blind-hole H1. The reflective electrodes 117 may have the same height as a distance from the connection substrate 113 to an upper surface of the p-type electrode 33.

[0089] Then, as shown in FIG. 3G, a transparent electrode 116 is formed to cover the p-type electrodes 33, the encapsulation material 125 and the reflective electrodes 117. The transparent electrode 116 may be formed by filling steps between the p-type electrodes 33, the encapsulation material 125 and the reflective electrodes 117.

[0090] As the transparent electrode 116 is formed as described above, manufacture of the light emitting diode part 110 according to this exemplary embodiment is completed.

[0091] FIG. 4A, FIG. 4B, and FIG. 4C are sectional views illustrating a process of coupling the light emitting part, the light conversion part, and the TFT panel part of the display apparatus according to the first exemplary embodiment.

[0092] After completion of manufacture of the light emitting part 111 through the processes shown in FIGS. 2A-2F and FIGS. 3A-3G, the light emitting part 111 may be coupled to the light conversion part 123 and the TFT panel part 130, which are separately manufactured. This process will be described with reference to FIGS. 4A-4C.

[0093] The TFT panel part 130 may be manufactured to have a large area and may be provided with a connection electrode 134 and a TFT circuit at a location corresponding to each subpixel. Thus, as shown in FIG. 4A, the light emitting part 111 having a smaller size than the TFT panel part 130 having a large area is coupled to the TFT panel part 130. In this exemplary embodiment, the TFT panel part 130 has an anisotropic conductive film 150 attached to an upper side thereof and the light emitting part 111 is disposed on the anisotropic conductive film 150 such that the conductive portions 113a of the connection substrate 113 adjoin the connection electrodes 134, respectively. In addition, the light emitting part 111 is coupled to the TFT panel part 130 by imparting force from above the light emitting part 111 towards the TFT panel part 130. Here, the anisotropic conductive film 150 is compressed such that the conductive portions 113a of the connection substrate 113 can be electrically connected to the connection electrodes 134.

[0094] After one light emitting part 111 is coupled to the TFT panel part 130 having a large area, another light emitting part 111 is coupled to the TFT panel part 130 so as to be adjacent to the light emitting part 111 coupled to the TFT panel part 130. As a result, the light emitting parts 111 are coupled to the TFT panel part 130, as shown in FIG. 4B.

[0095] After completion of coupling a plurality of light emitting parts 111 to the TFT panel part 130, the light conversion part 123 is coupled to upper sides of the light emitting parts 111, as shown in FIG. 4C. Here, the light conversion part 123 is coupled thereto such that the phosphor layer 126 contacts the transparent electrode 116. In this exemplary embodiment, the light conversion part 123 may also be manufactured to have a large area like the TFT panel part 130.

[0096] As such, the light conversion part 123 having a large area is coupled to the plurality of light emitting parts 111, thereby providing a finished display apparatus 100.

[0097] FIG. 5 is a sectional view of a display apparatus according to a second exemplary embodiment.

[0098] Referring to FIG. 5, the display apparatus 100 according to the second exemplary embodiment includes a light emitting diode part 110, a TFT panel part 130, and an anisotropic conductive film 150.

[0099] The light emitting diode part 110 includes a light emitting part 111 and a light conversion part 123. The light emitting part 111 includes light emitting diodes 112, a connection substrate 113, a transparent electrode 116, reflective electrodes 117, and an encapsulation material 125. The light conversion part 123 includes a phosphor layer 126, a color filter 127, and a protective substrate 128. In description of the second exemplary embodiment, descriptions of the same components as the first exemplary embodiment will be omitted.

[0100] In this exemplary embodiment, the light emitting part 111 includes a plurality of light emitting diodes 112,



each of which includes an n-type semiconductor layer 23, an active layer 25, a p-type semiconductor layer 27, and an n-type electrode 31. Unlike the first exemplary embodiment, the light emitting diode 112 according to this exemplary embodiment does not include the p-type electrode 33. As described below, the p-type semiconductor layer 27 of the light emitting diode 112 according to this exemplary embodiment may have a width of greater than 10  $\mu\text{m}$ . That is, an upper surface of the p-type semiconductor layer 27 may have an area of larger than 100  $\mu\text{m}^2$ . However, it should be noted that the size of the light emitting diode 112 does not increase without limitation and may be determined so as to be received in a subpixel.

[0101] In this exemplary embodiment, each of the light emitting diodes 112 is surrounded by the encapsulation material 125 and the upper side of the light emitting diode 112 may also be covered by the encapsulation material 125. Here, the upper side of the light emitting diode 112 may be partially covered by the encapsulation material 125 such that an upper side of the p-type semiconductor layer 27 can be partially exposed. An exposed area of the p-type semiconductor layer 27 may be small, as compared with the overall area of the p-type semiconductor layer 27. By way of example, when the p-type semiconductor layer 27 has a total area of 100  $\mu\text{m}^2$ , the exposed region of the p-type semiconductor layer 27 may have an area of larger than 0.1  $\mu\text{m}^2$  to 25  $\mu\text{m}^2$ .

[0102] The transparent electrode 116 is disposed to cover the reflective electrodes 117 and the encapsulation material 125 and may electrically contact the p-type semiconductor layer 27 exposed through the encapsulation material 125. With this structure, even when small current is supplied to the p-type semiconductor layer 27, it is possible to maintain current density of a certain level or more since the contact area between the p-type semiconductor layer 27 and the transparent electrode 116 is relatively small.

[0103] With this structure of the light emitting diode 112, light emitted from the light emitting diodes 112 can be discharged through the upper and side surfaces of the light emitting diodes 112. Light emitted from the side surfaces of the light emitting diode 112 is reflected by the connection substrate 113 and the reflective electrodes 117 to be discharged upwards.

[0104] FIG. 6A, FIG. 6B, FIG. 6C, FIG. 6D, FIG. 6E, FIG. 6F, and FIG. 6G are sectional views illustrating a process of manufacturing the light emitting diodes of the display apparatus according to the second exemplary embodiment. FIG. 7A, FIG. 7B, FIG. 7C, FIG. 7D, FIG. 7E, and FIG. 7F are sectional views illustrating a process of manufacturing the light emitting part of the display apparatus according to the second exemplary embodiment.

[0105] The process of manufacturing the light emitting diodes 112 according to this exemplary embodiment will be described with reference to FIGS. 6A-6G. The process shown in FIGS. 6A, 6B, and 6C is the same as that of the first exemplary embodiment and a description thereof will be omitted. Referring to FIG. 6C, after the plurality of light emitting diodes 112 is formed with reference to the p-type electrodes 33, the p-type electrodes 33 are removed from the plurality of light emitting diodes 112. FIG. 6D shows the structure wherein the p-type electrodes 33 are removed from the light emitting diodes 112.

[0106] Referring to FIG. 6E, after removal of the p-type electrodes 33, the plurality of light emitting diodes 112 is

covered with a filler 125a. Then, as shown in FIG. 6F, a second manufacturing substrate 21b is bonded to an upper side of the filler 125a. After bonding of the second manufacturing substrate 21b, the first manufacturing substrate 21a is removed, as shown in FIG. 6G.

[0107] Then, as shown in FIG. 7A, a connection substrate 113 is brought into contact with and coupled to the semiconductor structure from which the first manufacturing substrate 21a is removed. Here, a bonding agent may be applied to a portion of an upper surface of the connection substrate 113, particularly, to some conductive portions 113a of the connection substrate 113.

[0108] As a result, referring to FIG. 7B, the plurality of light emitting diodes 112 is coupled to the conductive portions 113a of the connection substrate 113, and an encapsulation material 125 is formed to cover the plurality of light emitting diodes 112 bonded to the connection substrate 113, as shown in FIG. 7C.

[0109] Next, as shown in FIG. 7D, first blind-holes H1 and second blind-holes H2 are formed by etching the encapsulation material 125. Here, the first blind-holes H1 are formed to expose the conductive portions 113a of the connection substrate 113 between the light emitting diodes 112 as in the first exemplary embodiment. The second blind-hole H2 is formed on each of the light emitting diodes 112 so as to expose a portion of the p-type semiconductor layer 27 of the light emitting diode 112. By way of example, when the p-type semiconductor layer 27 has a total area of 100  $\mu\text{m}^2$ , the exposed portion of the p-type semiconductor layer 27 may have an area of larger than 0.1  $\mu\text{m}^2$  to 25  $\mu\text{m}^2$ .

[0110] After formation of the first blind-holes H1 and the second blind-holes H2, reflective electrodes are formed on the first blind-holes H1, as shown in FIG. 7E. The reflective electrodes 117 are formed in the same way as the first exemplary embodiment and may have a greater height than the encapsulation material 125.

[0111] Then, as shown in FIG. 7F, a transparent electrode 116 is formed to cover the exposed portion of the p-type semiconductor layer 27, the encapsulation material 125 and the reflective electrodes 117. The transparent electrode 116 fills the second blind-holes H2 formed in the encapsulation material 125 to form electrical contact with the p-type semiconductor layer 27. The transparent electrode 116 may be formed by completely filling steps formed between the encapsulation material 125 and the reflective electrodes 117.

[0112] When the transparent electrode 116 is formed as described above, manufacture of the light emitting part 111 is completed. The process of coupling the light emitting part 111 to the TFT panel part 130 and the light conversion part 123 is the same as the first exemplary embodiment and detailed descriptions thereof will be omitted.

[0113] FIG. 8 is a sectional view of a display apparatus according to a third exemplary embodiment.

[0114] Referring to FIG. 8, the display apparatus 100 according to the third exemplary embodiment includes a light emitting diode part 110, a TFT panel part 130, and an anisotropic conductive film 150.

[0115] The light emitting diode part 110 includes a light emitting part 111 and a light conversion part 123. The light emitting part 111 includes light emitting diodes 112, a connection substrate 113, reflective electrodes 117, and an encapsulation material 125. The light conversion part 123 includes a phosphor layer 126, a color filter 127, and a protective substrate 128.

[0116] The light emitting part 111 includes a plurality of light emitting diodes 112, which are regularly arranged with reference to the connection substrate 113. In this exemplary embodiment, light emitting diodes 112 are flip-chip type light emitting diodes 112. That is, referring to FIG. 8, each of the light emitting diodes 112 includes an n-type semiconductor layer 23, an active layer 25, a p-type semiconductor layer 27, an n-type electrode 31, and a p-type electrode 33. The p-type electrode 33 electrically contacts the p-type semiconductor layer 27, and the n-type semiconductor layer 23 may be partially exposed by etching the p-type semiconductor layer 27 and the active layer 25 at one side of the p-type electrode 33. The n-type electrode 31 may be formed on the exposed portion of the n-type semiconductor layer 23. The n-type electrode 31 may be formed with a large thickness so as to be flush with the p-type electrode 33.

[0117] By forming the light emitting diodes 112 as described above, the p-type electrode 33 and the n-type electrode 31 of each of the light emitting diodes 112 can electrically contact a corresponding conductive portion 113a of the connection substrate 113.

[0118] As in the first exemplary embodiment, the connection substrate 113 according to this exemplary embodiment includes conductive portions 113a and insulating portions 113b, in which the distance between the conductive portions 113a may be different from that of the first exemplary embodiment. This is because the p-type electrode 33 and the n-type electrode 31 of each light emitting diode 112 electrically contact each of the conductive portions 113a of the connection substrate 113.

[0119] As in the first and second exemplary embodiments, the encapsulation material 125 is disposed between the reflective electrodes 117 to cover the light emitting diodes 112, and may also be disposed between the n-type electrode 31 and the p-type electrode 33 to insulate the n-type electrode 31 from the p-type electrode 33.

[0120] In this exemplary embodiment, since both the n-type electrode 31 and the p-type electrode 33 electrically contact the conductive portion 113a of the connection substrate 113, the transparent electrode 116 may be omitted. That is, the encapsulation material 125 is formed to completely cover the light emitting diode 112. In addition, the reflective electrodes 117 disposed between the encapsulation materials 125 have the same height as the encapsulation materials 125. With this structure, the light conversion part 123 can be directly coupled to upper sides of the encapsulation material 125 and the reflective electrodes 117.

[0121] With the structure of the display apparatus 100 according to this exemplary embodiment manufactured as above, light emitted from each of the light emitting diodes 112 can be discharged through the upper and side surfaces of the light emitting diode 112. Light emitted from the light emitting diodes 112 can be directly discharged towards the light conversion part 123 or can be reflected by the reflective electrodes 117 or by the connection substrate 113 to be discharged towards the light conversion part 123.

[0122] FIG. 9 is a sectional view of a display apparatus according to a fourth exemplary embodiment.

[0123] Referring to FIG. 9, the display apparatus 100 according to the fourth exemplary embodiment includes a light emitting diode part 110, a TFT panel part 130, and an anisotropic conductive film 150.

[0124] The light emitting diode part 110 includes a light emitting part 111 and a light conversion part 123. The light emitting part 111 includes light emitting diodes 112, a connection substrate 113, a transparent electrode 116, reflective electrodes 117, and an encapsulation material 125. The light conversion part 123 includes a phosphor layer 126, a color filter 127, and a protective substrate 128. In description of this exemplary embodiment, descriptions of the same components as in the first exemplary embodiment will be omitted.

[0125] In the light conversion part 123 according to this exemplary embodiment, the phosphor layer 126 includes a white phosphor layer 126f. The white phosphor layer 126f emits white light through wavelength conversion of light emitted from the light emitting diode 112. Thus, the components of the white phosphor layer 126f can be changed depending upon the kind of light emitted from the light emitting diodes 112.

[0126] White light emitted through the white phosphor layer 126f is converted into blue light, green light and red light while passing through the blue light portion 127a, the green light portion 127b and the red light portion 127c of the color filter 127 such that only blue light, green light and red light can be discharged to the outside.

[0127] FIG. 10 is a sectional view of a display apparatus according to a fifth exemplary embodiment.

[0128] Referring to FIG. 10, the display apparatus 100 according to the fifth exemplary embodiment includes a light emitting diode part 110, a TFT panel part 130, and an anisotropic conductive film 150.

[0129] The light emitting diode part 110 includes a light emitting part 111 and a light conversion part 123. The light emitting part 111 includes light emitting diodes 112, a connection substrate 113, a transparent electrode 116, reflective electrodes 117, and an encapsulation material 125. The light conversion part 123 includes a phosphor layer 126, a color filter 127, and a protective substrate 128. In description of this exemplary embodiment, descriptions of the same components as the first and fourth exemplary embodiments will be omitted.

[0130] As in the fourth exemplary embodiment, the phosphor layer 126 of the light conversion part 123 according to the fifth exemplary embodiment includes a white phosphor layer 126f, and the color filter 127 includes a blue light portion 127a, a green light portion 127b, a red light portion 127c, and a transparent portion 127e. In this exemplary embodiment, each of the blue light portion 127a, the green light portion 127b, the red light portion 127c and the transparent portion 127e may constitute one subpixel and one pixel may be composed of four subpixels.

[0131] Accordingly, white light emitted through the phosphor layer 126 is converted into blue light, green light and red light while passing through the blue light portion 127a, the green light portion 127b and the red light portion 127c such that only blue light, green light and red light can be discharged to the outside, and white light passing through the transparent portion 127e can be discharged to the outside without wavelength conversion.

[0132] FIG. 11 is a sectional view of a display apparatus according to a sixth exemplary embodiment.

[0133] Referring to FIG. 11, the display apparatus 100 according to the sixth exemplary embodiment includes a light emitting diode part 110, a TFT panel part 130, and an anisotropic conductive film 150.

[0134] The light emitting diode part **110** includes a light emitting part **111** and a light conversion part **123**. The light emitting part **111** includes light emitting diodes **112**, a connection substrate **113**, a transparent electrode **116**, reflective electrodes **117**, and an encapsulation material **125**. The light conversion part **123** includes a phosphor layer **126**, a color filter **127**, and a protective substrate **128**. In description of this exemplary embodiment, descriptions of the same components as the first exemplary embodiment will be omitted.

[0135] In the light conversion part **123** according to this exemplary embodiment, the phosphor layer **126** includes a red-green phosphor layer **126bc** and a transparent layer **126e**. The red-green phosphor layer **126bc** includes green phosphors and red phosphors. Accordingly, the red-green phosphor layer **126bc** emits a mixture of green light and red light through wavelength conversion of light emitted from the light emitting diode **112**. In this exemplary embodiment, the light emitting diodes **112** are blue light emitting diodes and blue light emitted from the light emitting diode **112** is subjected to wavelength conversion while passing through the red-green phosphor layer **126bc** such that green light and red light can be discharged at the same time.

[0136] Green light and red light emitted through the red-green phosphor layer **126bc** can be discharged through the green light portion **127b** and the red light portion of the color filter **127** such that only green light and red light can be discharged to the outside. That is, the red-green phosphor layer **126bc** may be disposed at locations corresponding to the green light portion **127b** and the red light portion **127c** of the color filter **127**.

[0137] Further, the transparent layer **126e** of the phosphor layer **126** may be disposed at a location corresponding to the blue light portion **127a** of the color filter **127**.

[0138] FIG. **12** is a sectional view of a display apparatus according to a seventh exemplary embodiment.

[0139] Referring to FIG. **12**, the display apparatus **100** according to the seventh exemplary embodiment includes a light emitting diode part **110**, a TFT panel part **130**, and an anisotropic conductive film **150**.

[0140] The light emitting diode part **110** includes the light emitting part **111**, which includes blue light emitting diodes **112a**, green light emitting diodes **112b**, red light emitting diodes **112c**, a connection substrate **113**, a transparent electrode **116**, reflective electrodes **117**, and an encapsulation material **125**. In description of this exemplary embodiment, descriptions of the same components as the first exemplary embodiment will be omitted.

[0141] Multiple blue light emitting diodes **112a**, the green light emitting diodes **112b** and the red light emitting diodes **112c** are provided. Each of the blue light emitting diode **112a**, the green light emitting diode **112b** and the red light emitting diode **112c** is regularly arranged on the connection substrate **113**. In this exemplary embodiment, one blue light emitting diode **112a**, one green light emitting diode **112b** and one red light emitting diode **112c** may be disposed adjacent to one another and these light emitting diodes **112a**, **112b**, **112c** may be arranged at constant intervals in rows and columns to be separated from each other.

[0142] In this exemplary embodiment, one of the blue light emitting diode **112a**, the green light emitting diode **112b**, and the red light emitting diode **112c** is provided to one subpixel. The blue light emitting diode **112a** may emit light having a peak wavelength in the range of 430 nm to 470

nm and the green light emitting diode **112b** may emit light having a peak wavelength in the range of 510 nm to 550 nm. The red light emitting diode **112c** may emit light having a peak wavelength of 610 nm to 650 nm.

[0143] The encapsulation material **125** is disposed to surround the side surface of each of the blue light emitting diodes **112a**, the green light emitting diodes **112b**, and the red light emitting diodes **112c**. For the same reason as for the provision of the encapsulation material **125** in the other exemplary embodiments, the encapsulation material **125** can prevent damage to each of the light emitting diodes **112a**, **112b**, **112c** due to external environments and exhibits electrical insulating properties.

[0144] Accordingly, light emitted from the blue light emitting diodes **112a**, the green light emitting diodes **112b** and the red light emitting diodes **112c** can be discharged to the outside through the encapsulation material **125** and the transparent electrode **116**.

[0145] Unlike the other exemplary embodiments, the display apparatus **100** according to this exemplary embodiment may not include a separate light conversion part **123**. Since blue light, green light, and red light can be emitted from the light emitting diodes **112a**, **112b**, **112c** provided in one-to-one correspondence to subpixels, the display apparatus **100** can be driven by operation of the TFT panel part **130** without the separate light conversion part **123**.

[0146] Although some exemplary embodiments have been described herein, it should be understood by those skilled in the art that these embodiments are given by way of illustration only, and that various modifications, variations, and alterations can be made without departing from the spirit and scope of the invention. Therefore, the scope of the present disclosure should be limited only by the accompanying claims and equivalents thereof.

What is claimed is:

1. A display apparatus, comprising:

a light emitting part comprising a plurality of light emitting diodes; and

a thin film transistor (TFT) panel part comprising a plurality of TFTs configured to drive the plurality of light emitting diodes,

wherein a first side of the light emitting part and a first side of the TFT panel part are coupled to each other so as to face each other, and

wherein the plurality of light emitting diodes are electrically connected to the plurality of TFTs, respectively.

2. The display apparatus according to claim 1, further comprising a light conversion part configured to convert light emitted from the light emitting part, wherein a second side of the light emitting part is coupled to one side of the light conversion part to face each other.

3. The display apparatus according to claim 2, wherein the plurality of light emitting diodes is configured to emit light in the near ultraviolet range or blue light, and the light conversion part is configured to emit at least one of blue light, green light, and red light through wavelength conversion of light emitted from the plurality of light emitting diodes.

4. The display apparatus according to claim 2, wherein the light conversion part comprises:

a phosphor layer configured to convert wavelengths of light emitted from the plurality of light emitting diodes; and

a color filter disposed on the phosphor layer and configured to block light emitted from the phosphor layer outside of a wavelength range.

5. The display apparatus according to claim 1, wherein the plurality of light emitting diodes comprise at least one of a blue light emitting diode configured to emit blue light, a green light emitting diode configured to emit green light, and a red light emitting diode configured to emit green light.

6. The display apparatus according to claim 1, wherein the light emitting part comprises:

- a connection substrate comprising a plurality of conductive portions disposed between insulating portions electrically insulated from each other; and

- a plurality of reflective electrodes disposed to surround the plurality of light emitting diodes so as to be separated from side surfaces of the plurality of light emitting diodes,

wherein the plurality of light emitting diodes is disposed on the connection substrate and electrically connected to a first set of conductive portions among the plurality of conductive portions, and

wherein the plurality of TFTs is electrically connected to the plurality of light emitting diodes through the connection substrate.

7. The display apparatus according to claim 6, wherein the plurality of reflective electrodes is electrically connected to a second set of conductive portions among the plurality of conductive portions.

8. The display apparatus according to claim 6, wherein the connection substrate is a flexible substrate.

9. The display apparatus according to claim 6, wherein: the insulating portions comprise at least one of polydimethylsiloxane (PDMS) and a polyimide; and

the conductive portions comprise a metal.

10. The display apparatus according to claim 6, wherein each of the light emitting diodes comprises:

- a light emitting structure comprising a first conductivity type semiconductor layer, a second conductivity type semiconductor layer, and an active layer interposed between the first and second conductivity type semiconductor layers;

- a first electrode covering the first conductivity type semiconductor layer and electrically connected to the first conductivity type semiconductor layer;

- a second electrode covering the second conductivity type semiconductor layer and electrically connected to the second conductivity type semiconductor layer; and

- a transparent electrode disposed on the plurality of light emitting diodes and electrically connected to the second electrode.

11. The display apparatus according to claim 10, wherein each of the light emitting diodes has a width of 10  $\mu\text{m}$  or less.

12. The display apparatus according to claim 10, wherein: each of the light emitting diodes further comprises an encapsulation material filling spaces between the plurality of reflective electrodes and the plurality of light emitting diodes; and

the transparent electrode is electrically connected to the second electrode exposed from an upper side of the encapsulation material.

13. The display apparatus according to claim 6, wherein each of the light emitting diodes comprises:

- a light emitting structure comprising a first conductivity type semiconductor layer, a second conductivity type semiconductor layer, and an active layer interposed between the first and second conductivity type semiconductor layers;

- a first electrode disposed to cover the first conductivity type semiconductor layer and electrically connected to the first conductivity type semiconductor layer; and

- a transparent electrode disposed on the plurality of light emitting diodes and electrically connected to the second conductivity type semiconductor layer.

14. The display apparatus according to claim 13, wherein each of the light emitting diodes further comprises encapsulation materials each disposed between the plurality of reflective electrodes and covering each of the light emitting diodes, the encapsulation materials exposing a portion of the second conductivity type semiconductor layer therebetween, and the transparent electrode is electrically connected to the second conductivity type semiconductor layer exposed between the encapsulation materials.

15. The display apparatus according to claim 13, wherein each of the light emitting diodes has a width greater than 10  $\mu\text{m}$  but less than a distance between the reflective electrodes.

16. The display apparatus according to claim 6, wherein each of the light emitting diodes comprises:

- a light emitting structure comprising a first conductivity type semiconductor layer, a second conductivity type semiconductor layer, and an active layer interposed between the first and second conductivity type semiconductor layers, wherein a portion of the first conductivity type semiconductor layer is exposed;

- a first electrode electrically connected to the partially exposed first conductivity type semiconductor layer; and

- a second electrode disposed to cover the second conductivity type semiconductor layer and electrically connected to the second conductivity type semiconductor layer, and

wherein the first and second electrodes are electrically connected to the plurality of conductive portions, respectively.

17. The display apparatus according to claim 16, wherein each of the light emitting diodes further comprise an encapsulation material filling spaces between the plurality of reflective electrodes and the plurality of light emitting diodes and disposed between the first and second electrodes to insulate the first and second electrodes from each other.

18. A display apparatus comprising:

- a plurality of light emitting parts each comprising a plurality of light emitting diodes; and

- a thin film transistor (TFT) panel part comprising a plurality of TFTs configured to drive the plurality of light emitting diodes,

wherein a first side of the plurality of light emitting parts is coupled to the TFT panel part so as to face each other and the plurality of light emitting diodes is electrically connected to some of the plurality of TFTs, respectively.

19. The display apparatus according to claim 18, further comprising:

- a light conversion part configured to convert light emitted from the plurality of light emitting parts,

the light conversion part is disposed to cover a second side of each of the light emitting parts.

20. The display apparatus according to claim 19, wherein each light emitting diode, among the plurality of light emitting diodes, has a width of 10  $\mu\text{m}$  or less.

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